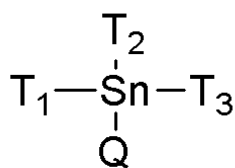


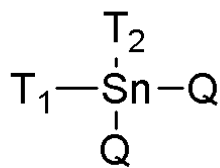
TITLE OF INVENTION: COMPOUND FOR FORMING METAL-CONTAINING
FILM, COMPOSITION FOR FORMING METAL-CONTAINING FILM,
PATTERNING PROCESS, AND SEMICONDUCTOR PHOTORESIST
MATERIAL

ABSTRACT

A compound for forming a metal-containing film to be contained in a composition for forming a metal-containing film used in manufacturing a semiconductor, where the compound for forming a metal-containing film is represented by the following general formula (M-1) or (M-2). This provides: a compound for forming a metal-containing film having better dry etching resistance than conventional resist underlayer film materials and also having high filling and planarizing properties; a composition for forming a metal-containing film containing the compound; a patterning process in which the composition is used as a resist underlayer film material; a patterning process in which the composition is used as a resist material; and a semiconductor photoresist material containing the composition.



(M-1)



(M-2)

[Fig.1]